TOSHIBA HIGH EFFICIENCY DIODE STACK (HED) SILICON EPITAXIAL TYPE

U 2 0 G L 2 C 4 8 A

SWITCHING TYPE POWER SUPPLY APPLICATION

CONVERTER & CHOPPER APPLICATION

Repetitive Peak Reverse Voltage $: V_{RRM} = 400V$

Average Output Rectified Current: IO=20A

Ultra Fast Reverse-Recovery Time: trr=35ns (Max.)

Low Switching Losses and Output Noise.

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT		
Repetitive Peak Reverse Voltage	v_{RRM}	400	V		
Average Output Rectified Current	IO	20	A		
Peak One Cycle Surge Forward	Traces	100 (50Hz)	A		
Current (Sin Wave)	I_{FSM}	110 (60Hz)	A		
Junction Temperature	$\mathbf{T}_{\mathbf{j}}$	-40~150	°C		
Storage Temperature Range	$\mathrm{T_{stg}}$	-40~150	°C		

Unit in mm 9. 2.54 ± 0.25 ANODE ANODE CATHODE **JEDEC EIAJ**

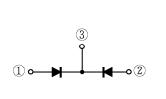
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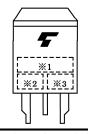
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Peak Forward Voltage	$ m V_{FM}$	$I_{\text{FM}} = 10 \text{A}$	_	_	1.8	V
Repetitive Peak Reverse Current	I_{RRM}	$V_{RRM} = 400V$	_	_	50	μ A
Reverse Recovery Time	t_{rr}	$I_F=2A$, di/dt= $-50A/\mu s$	_	<u> </u>	35	ns
Forward Recovery Time	t_{fr}	$I_{\mathbf{F}} = 1A$	_	_	100	ns
Thermal Resistance	$ m R_{th~(j-c)}$	DC Total, Junction to Case	_	_	1.6	°C/W

(Note) VFM, IRRM, trr, tfr ... A value of one cell.

Polarity Marking





%1	MARK	20GL2C		
%2	A			
%3	Lot Number			

TOSHIBA

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